

2nd announcement

XIII International Autumn Meeting

„Gettering and Defect Engineering in Semiconductor Technology“

G A D E S T 2 0 0 9

September 26 - October 02, 2009

in

Döllnsee-Schorfheide

north of Berlin, Germany



Topics

GADEST 2009 will encourage but not limit submissions to the following topics

- Large diameter crystal growth
- Crystalline silicon for solar cells: single crystals, multi-crystalline Si, ribbons, Si thin films on substrates
- Influence of Si feedstock quality on solar cell performance
- Silicon-based materials and advanced semiconductor materials (strained Si, SOI, SiGe, SiC, Ge)
- Impurities in Si: oxygen, carbon, nitrogen, fluorine, metals
- Modeling and simulation of defects in Si/semiconductors
- Defect engineering in microelectronics and photovoltaics
- Gettering and hydrogen passivation
- Defect and impurity characterization (physical and electrical)
- Nanostructures and devices: nanocrystals, nanowires, quantum dots
- Silicon-based heterostructures
- Strain engineered materials
- Silicon-based photonics and photonic crystals
- Defect aspects for new devices: co-integration of Ge and III-V, graphenes, organo-silica devices

Dates and deadlines

Abstract submission	January 30, 2009
Notification of acceptance	March, 2009
Manuscript due *)	June 05, 2009
Regular registration	June 26, 2009
Late registration	September 04, 2009
Conference	September 26 – October 02, 2009

*) The printed proceedings volume (in Solid State Phenomena) will be delivered to the participants at the beginning of the conference.

Contact

GADEST 2009 will be organized by

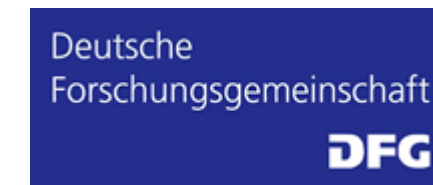
IHP - Innovations for High Performance Microelectronics

For further information, please contact the GADEST 2009 conference office at:

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Sponsors



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List of invited speakers (preliminary)

E. Astrova, Ioffe Inst., St. Petersburg, Russia

M. Bertoni, MIT Cambridge, USA

A. Boukai, Univ. of Berkeley, USA

O. Breitenstein, MPI Halle, Germany

A. Cavallini, Univ. of Bologna, Italy

Jun Chen, NIMS Tsukuba, Japan

S. Coffa, STMicroelectronics, Catania, Italy

P. Fath, centrotherm photovoltaics AG, Germany

G. Hahn, Univ. Konstanz, Germany

K. Kakimoto, Kyushu Univ., Fukuoka, Japan

O. Kononchuk, SOITEC Bernin, France

J. Kouvetakis, Arizona State Univ., USA

V. Kveder, RAS, Chernogolovka, Russia

M. Lemme, Harvard Univ., USA

A. Luque, Univ. Politecnica de Madrid, Spain

B. Pichaud, IM2NP, Univ. of Marseille, France

P. Pichler, Fraunhofer IISB, Erlangen, Germany

M. Reiche, MPI Halle, Germany

+ **J. Hoentschel**, AMD Dresden, Germany

Yuepeng Wan, LDK Solar Co., Jiangxi, China

Deren Yang, Zhejiang Univ., China

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R. Falster, London, UK

N. Inoue, Osaka, Japan

W. Koch, Dinkelsbühl, Germany

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V. Kveder, Chernogolovka, Russia

V. Litovchenko, Kiev, Ukraine

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D. Yang, Hangzhou, P.R. China

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